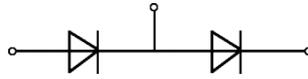


## Diode modules

## PSKD 802M

$I_{F(AV)} = 800 \text{ A}$   
 $V_{RRM} = 800-1800 \text{ V}$

### Preliminary Data Sheet



$V_{RSM}$ V	$V_{RRM}$ V	Type
900	800	PSKD 802M/08
1100	1000	PSKD 802M/10
1300	1200	PSKD 802M/12
1500	1400	PSKD 802M/14
1700	1600	PSKD 802M/16
1900	1800	PSKD 802M/18

Symbol	Test Conditions	Maximum Ratings
$I_{F(AV)}$	$T_C = 100^\circ\text{C}$ , module	800 A
$I_{F(RMS)}$		1256 A
$I_{FSM}$	$T_{VJ} = 150^\circ\text{C}$ t = 10 ms half sine	22000 A
$\int i^2 dt$	$T_{VJ} = 150^\circ\text{C}$ t = 10 ms half sine	2420 $\text{A}^2 \text{s} \cdot 10^3$
$T_{VJ}$		-40 ... + 150 $^\circ\text{C}$
$T_{VJM}$		150 $^\circ\text{C}$
$T_{stg}$		-40 ... + 125 $^\circ\text{C}$
$V_{ISOL}$	50 Hz, RMS t = 1 min $I_{ISOL} \leq 1 \text{ mA}$	min. 3000 V ~
$M_d$	Mounting torque (M6)	6,0 Nm
	Terminal connection torque (M5)	4,0 Nm
Weight	typ.	3360 g

### Features

- Isolated mounting base 3000V~
- Pressure contact technology with increased power cycling capability

### Applications

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

### Advantages

- Easy to mount
- Space and weight savings
- Improved temperature and power cycling capability

### Package, style and outline

Dimensions in mm (1mm = 0.0394")

Symbol	Test Conditions	Characteristic Value
$I_{RRM}$	at $V_{RRM}$ $T_{VJ} = 150^\circ\text{C}$	$\leq 45 \text{ mA}$
$V_{FM}$	$I_{FM} = 2400 \text{ A}$ $T_{VJ} = 25^\circ\text{C}$	$\leq 1,8 \text{ V}$
$V_{FO}$	For power-loss calculations only	0,72 V
$r_f$	$T_{VJ} = T_{VJM}$	0,18 m $\Omega$
$R_{th(j-c)}$	Per chip; Single side cooled	0,058 $^\circ\text{C/W}$

